FEISEM-I (Rev) A.P. I.

AGJ-2nd half (I)-12-15

Con. 9049-12.

(REVISED COURSE)

KR-3447

(2 Hours)

[Total Marks: 60

N.B.:(1) Question No. 1 is compulsory.

- (2) Attempt any three questions from remaining questions No. 2 to 6.
- (3) Assume suitable data wherever required.
- (4) Figures to the right indicate marks.

1. Attempt any five :-

15

- (a) Explain the term lattice parameters of Cubic crystal.
- (b) What is the probability of an electron being thermally excited to conduction band in silicon at 20°C. The band gap energy is 1·12eV; Boltzmann constant is 1·38 x 10⁻²³ J/k.
- (c) Mobility of holes is 0.025 m²/V-sec. What would be the resistivity of P-type silicon if the Hall coefficient of the sample is 2.25 x 10⁻⁵ m³/C?
- (d) Define dielectrics, electric dipole and polarizability.
- (e) Differentiate between soft and hard magnetic materials.
- (f) Define 'Reverberation time'. Write sabine's formula and explain the terms in it.
 - (g) State the terms: magnetostriction effect; piezo-electric effect.
- 2. (a) Explain the formation of energy bands in solids. With neat energy band diagrams explain 8 extrinsic semiconductors.
 - (b) Draw the unit cell of HCP. What is its co-ordination number, atomic radius, and feffective number of atoms per unit cell. Also calculate its packing factor.
- 3. (a) What is hysteresis? Draw a hysteris loop for ferromagnetic material and explain the various important points on it. What is the technical significance of the area enclosed under it. For a transformer which kind of material will you prefer the one with small hysteresis area or the big one?
 - (b) Derive Bragg's law. Calculate the glancing angle on the plane (100) for a crystal of rock salt (a = 2.125 A°). Consider the case of 2^{nd} order maximum and $\lambda = 0.592$ A°.
- 4. (a) Calculate the number of atoms per unit cell of a metal having lattice parameter 2.9A° 5 and density 7.87 gm/cm³. Atomic weight of metal is 55.85, Avagadro number is 6.023 x 10²³/gm-mole.
 - (b) Prove that the Fermi level lies exactly at the centre of the forbidden energy gap in case of an intrinsic semiconductor.
 - (c) Explain ionic polarization and obtain polarizability (α_i) .

5

Con.	9049-KR-3447-12

2

5.	(b)	With neat diagram of a unit cell, explain the structure of BaTiO ₃ . What is Hall effect? Derive expression for Hall voltage. Explain the absorption coefficient of a hall. Calculate the change in intensity level when	4
		the intensity of sound increases 1000 times its original intensity.	•
ó.	(a)	In what sense real crystals differ from ideal crystals? Explain the point defects in crystals.	5
	(b)	Explain construction and working of a solar cell.	_
	(c)	Find the natural frequency of vibration of quartz plate of thickness 2mm. Given Young's modulus of quartz $Y = 8 \times 10^{10} \text{ N/m}^2$, density of quartz is 2650 kg/m ³ . Caculate the change in thickness required if the same plate is used to produce ultrasonic waves of frequency 3MHz.	5